

1. Scope

The present specifications shall apply to FMXA-1104S.

2. Outline

High Frequency Rectification

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification,etc

3. Flammability

UL94V-0(Equivalent)

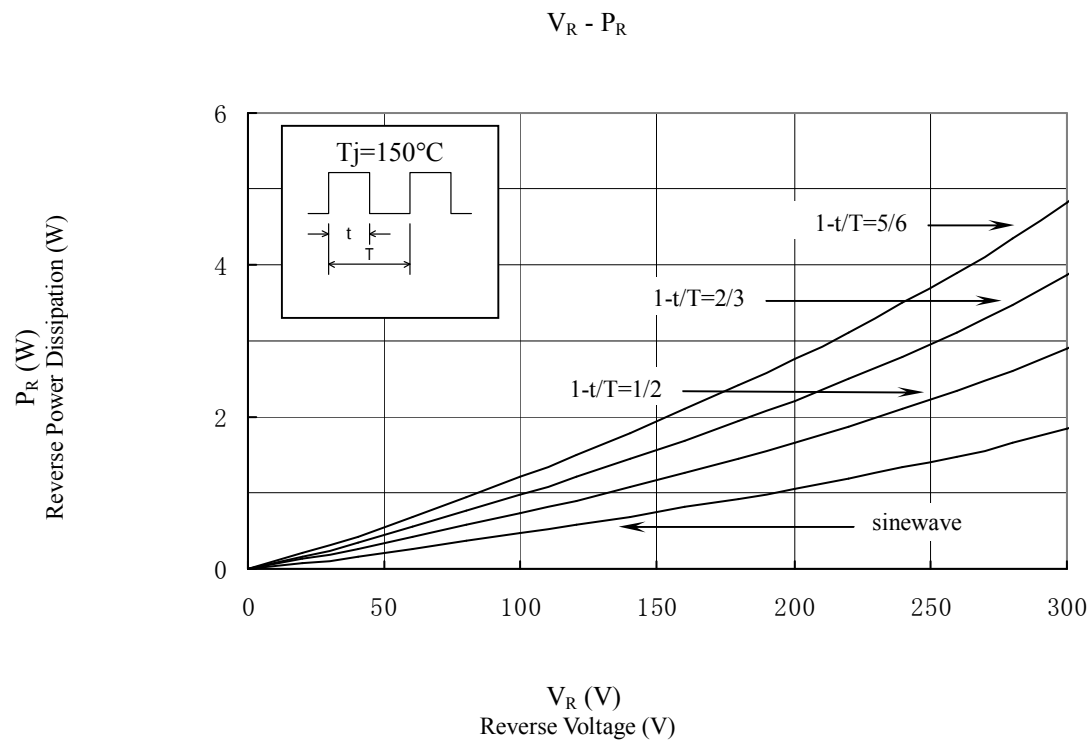
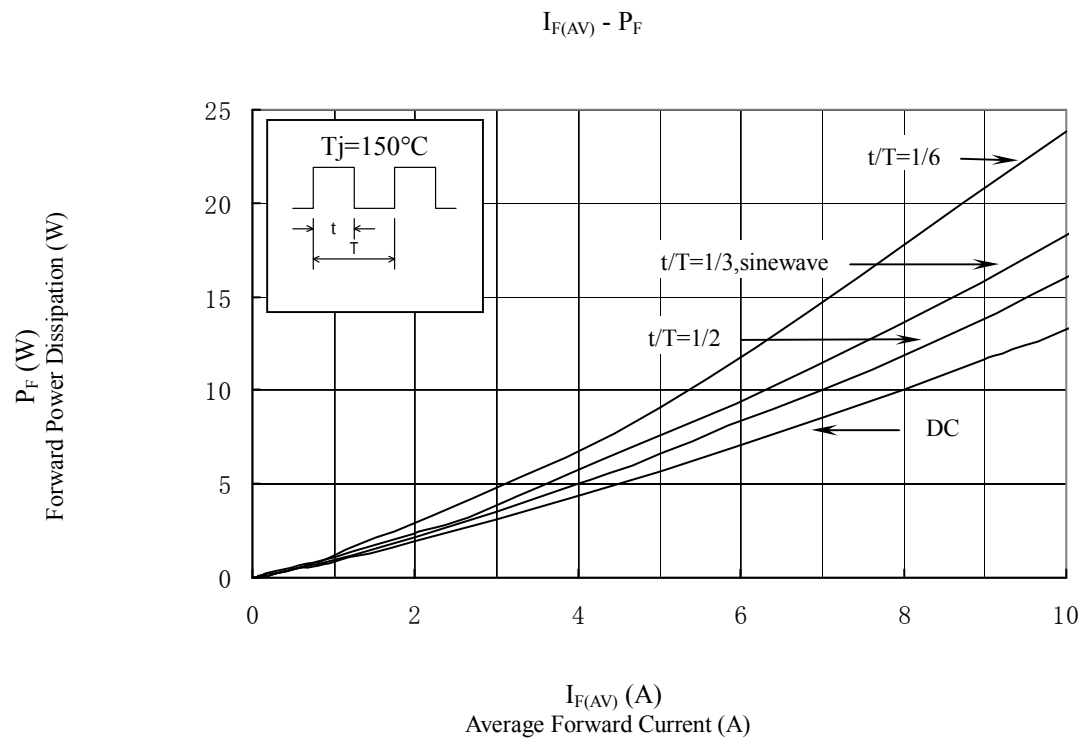
4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	400	
2	Peak Reverse Voltage	V_{RM}	V	400	
3	Average Forward Current	$I_{F(AV)}$	A	10	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	100	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	50	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	°C	-40 ~ +150	
7	Storage Temperature	T_{stg}	°C	-40 ~ +150	

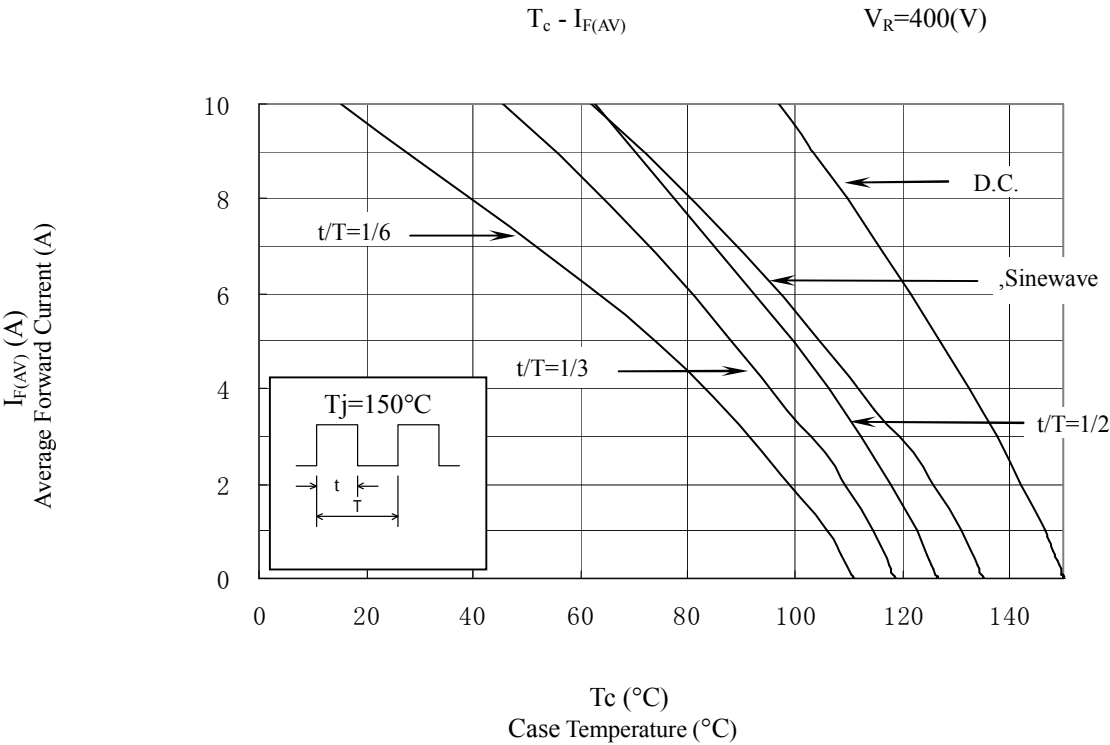
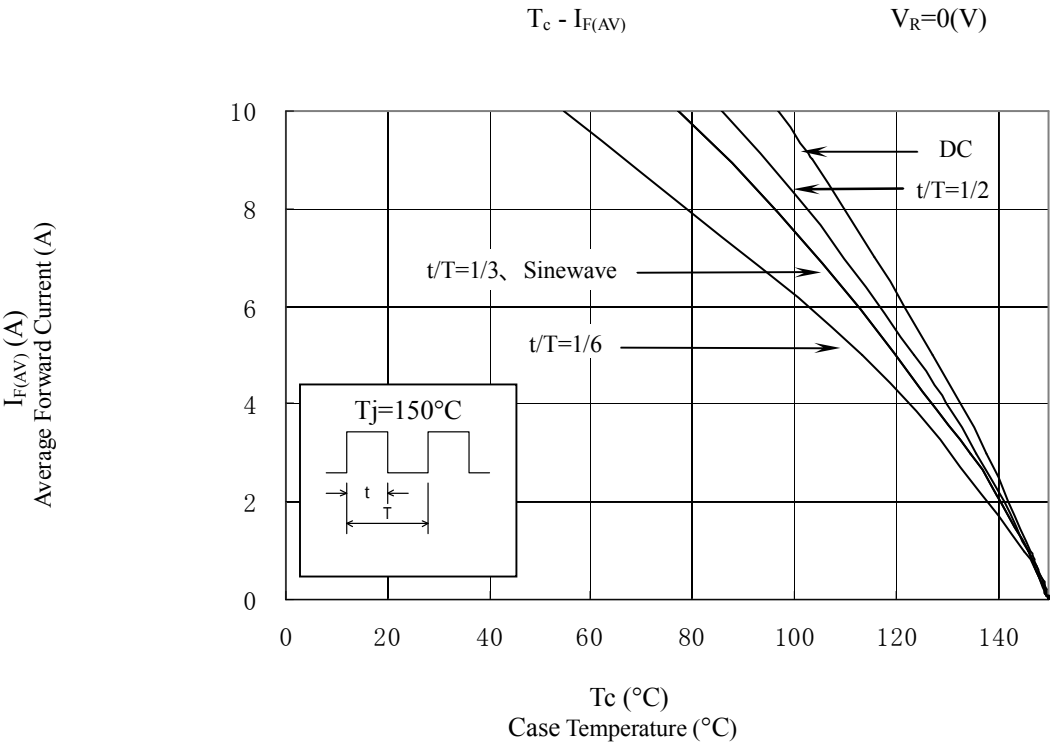
5. Electrical characteristics

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.50 max.	$I_F=10A$
2	Reverse Leakage Current	I_R	μA	100 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	30 max.	$V_R=V_{RM}$, $T_j=150^\circ C$
4	Reverse Recovery Time	$trr1$	ns	25 max.	$I_F=I_{RP}=500mA$ 90% Recovery point, $T_j=25^\circ C$
5	Thermal Resistance	$R_{th(j-c)}$	°C /W	4.0 max.	Between Junction and case

6. Characteristics

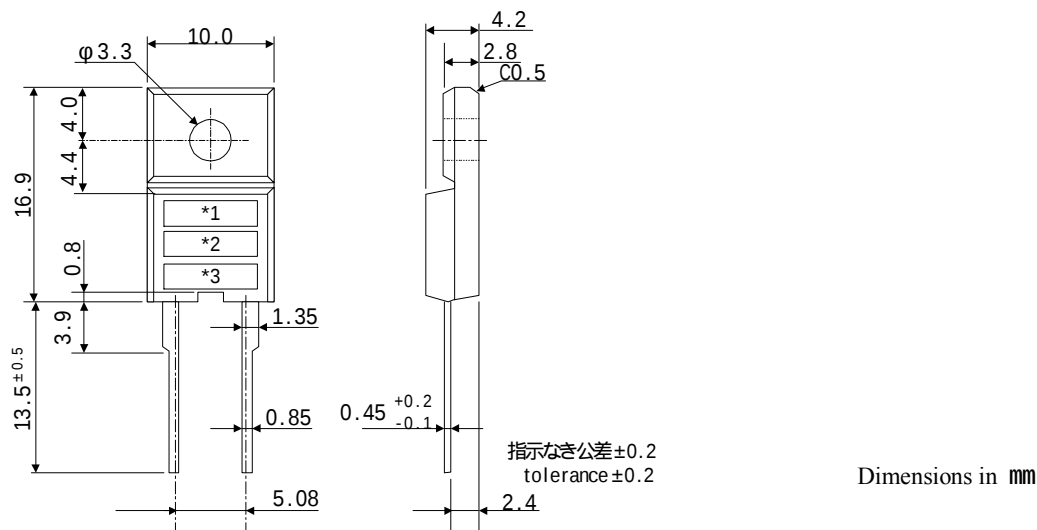


7. Derating



8. Package information

8-1Package type, physical dimensions and material



8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMXA-1104S	XA1104	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 4127 (Jan. 27, 2004)